

Complementary power Darlington transistors

Features

- Good h_{FE} linearity
- High f_T frequency
- Monolithic Darlington configuration with integrated antiparallel collector-emitter diode

Applications

■ Linear and switching industrial equipment

Description

The devices are manufactured in planar base island technology with monolithic Darlington configuration.

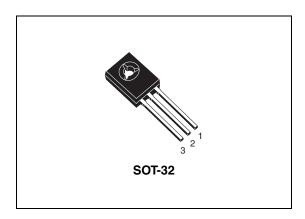


Figure 1. Internal schematic diagram

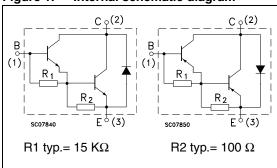


Table 1. Device summary

Order codes	Marking	Package	Packaging			
BD677	BD677					
BD677A	BD677A					
BD678	BD678					
BD678A	BD678A	SOT-32				
BD679	BD679		Tube			
BD679A	BD679A		Tube			
BD680	BD680					
BD680A	BD680A					
BD681	BD681					
BD682	BD682					

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1 Absolute maximum ratings

Table 2. Absolute maximum ratings

			Value			
Symbol	Parameter	NPN	BD677 BD677A	BD679 BD679A	BD681	Unit
		PNP	BD678 BD678A	BD680 BD680A	BD682	
V _{CBO}	CBO Collector-base voltage (I _E = 0)		60	80	100	V
V _{CEO}	Collector-emitter voltage (I _B = 0)		00	00	100	V
V _{EBO}	O Emitte-base voltage (I _C = 0)		5			V
I _C	I _C Collector current		4			Α
I _{CM}	I _{CM} Collector peak current		6			Α
I _B	I _B Base current		0.1			Α
P _{TOT}	P _{TOT} Total dissipation at T _{case} = 25°C		40			W
T _{stg}	Storage temperature		-65 to 150			°C
TJ	T _J Max. operating junction temperature		150			°C

Note: For PNP types voltage and current values are negative

Electrical characteristics BD6xxx

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C; unless otherwise specified)$

Table 3. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CEO}	Collector cut-off current (I _B = 0)	V_{CE} = half rated V_{CEO}			0.5	mA
I _{CBO}	Collector cut-off current (I _E = 0)	V_{CE} = rated V_{CBO} V_{CE} = rated V_{CBO} T_c = 100 °C			0.2	mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V			2	mA
		for BD677, BD677A, BD678, BD678A I _C = 50 mA	60			
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	for BD679, BD679A, BD680, BD680A I _C = 50 mA	80			V
		for BD681, BD682 I _C = 50 mA	100			
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation	for BD677, BD678, BD679, BD680, BD681, BD682 I _C = 1.5 A I _B = 30 mA			2.5	>
· CE(Sat)	voltage	for BD677A, BD678A, BD679A, BD680A I _C = 2 A I _B = 40 mA			2.8	
V _{BE} ⁽¹⁾	Base-emitter voltage	for BD677, BD678, BD679, BD680, BD681, BD682 I _C = 1.5 A V _{CE} = 3 V			2.5	V
· DE		for BD677A, BD678A, BD679A, BD680A I _C = 2 A V _{CE} = 3 V				

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Table 3. Electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
h _{FE} ⁽¹⁾	DC current gain	for BD677, BD678, BD679, BD680, BD681, BD682 I _C = 1.5 A V _{CE} = 3 V	750			
		for BD677A, BD678A, BD679A, BD680A I _C = 2 A V _{CE} = 3 V				

^{1.} Pulsed duration = 300 ms, duty cycle ≥1.5%.

Note: For PNP types voltage e current values are negative.

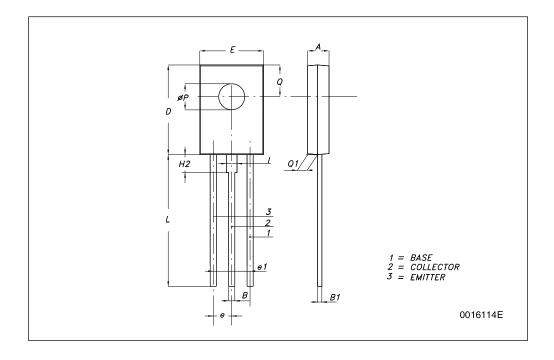
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark.

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SOT-32	(TO-126)) MECHANICAL DATA
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DIM.		mm.				
Diw.	MIN.	ТҮР	MAX.			
Α	2.4		2.9			
В	0.64		0.88			
B1	0.39		0.63			
D	10.5		11.05			
E	7.4		7.8			
е	2.04	2.29	2.54			
e1	4.07	4.58	5.08			
L	15.3		16			
Р	2.9		3.2			
Q		3.8				
Q1	1		1.52			
H2		2.15				
I		1.27				



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